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MANUFACTURE THEREOF CONDUCTOR LAYER AND (54) CONDUCTOR LAYER, CAPACITOR USING

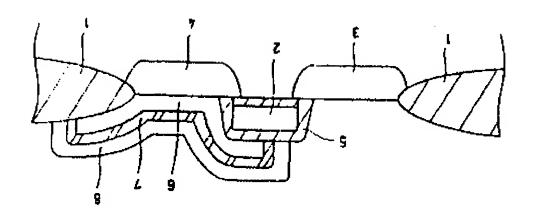
(57) Abstract:

electric field does not concentrate and forming the conductor layer by using PURPOSE: To obtain a conductor capacitor using said layer wherein dielectric strength is increased, by layer whose surface is flat, and a amorphous silicon containing no crystal grains. 5/10/01

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method, an amorphous silicon layer 6 oxygen is used as reaction gas. Vapor layer 6, the insulating layer 7 and the disilane or trisilane or tetrasilane and eliminated from the region except a amorphous silicon layer of excellent region in contact with drain 4. After an insulating layer 7 is formed, it is eliminated from the region except a risilane, and 300-400°C in the case composed of the amorphous silicon quality is formed on a substrate. By above gas, and its temperature is as growth is performed by heating the follows; 400-500°C in the case of disilane, 350-450°C in the case of insulating layer 7, and a capacitor CONSTITUTION: Mixed gas of is subjected to vapor growth on a of tetrasilane. Thus a flat surface region on the amorphous layer 6. formed, it is eliminated from the conductor layer composed of an MOS field effect transistor, and After a conductor layer 8 like a using the above manufacturing polycrystalline silicon layer is region except a region on the conducting layer 8 is formed.

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